

Infrared Emitting Diodes(GaAs)

KODENSHI

EL - 6F11

The EL - 6F11 is a high - power GaAs IRED mounted in a clear epoxy package. This IRED is both compact and easy to mount.

FEATURES

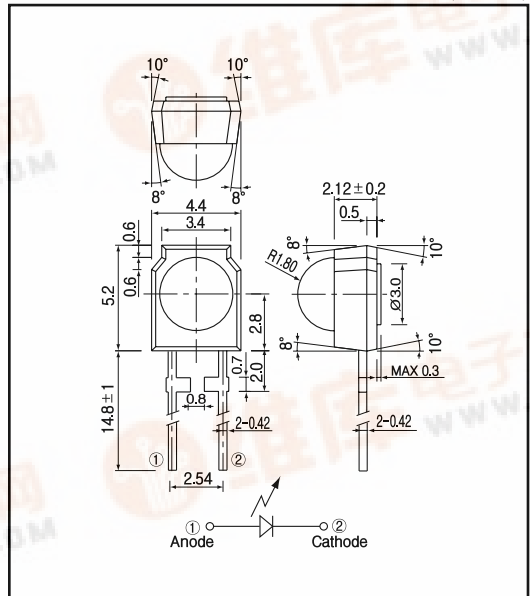
- Plastic mold package with a large caliber lens
- High output power

APPLICATIONS

- Optical switches

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

(Ta=25)

Item	Symbol	Rating	Unit
Reverse voltage	V _R	4	V
Forward current	I _F	50	mA
Power dissipation	P _o	80	mW
Pulse forward current ^{*1}	I _{FP}	1	A
Operating temp.	Topr.	- 25 +85	
Storage temp.	Tstg.	- 40 +85	
Soldering temp. ^{*2}	Tsol.	260	

*1. pulse width : tw 100 pec.period : T=10msec.

*2. For MAX.5 seconds at the position of 2 mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V _F	I _F =50mA		1.3	1.65	V
Reverse current	I _R	V _R =4V			10	μA
Peak emission wavelength	λ _p	I _F =20mA		940		nm
Spectral bandwidth		I _F =20mA		50		nm
Radiant intensity ^{*3}	P _o	I _F =50mA	2.5	6.0		V
Half angle		I _F =20mA		± 25		deg.

*3. Measured by tester of KODENSHI CORP.

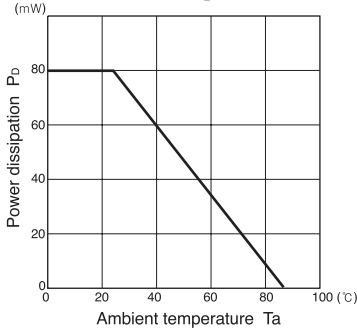


找零件就上维库电子市场

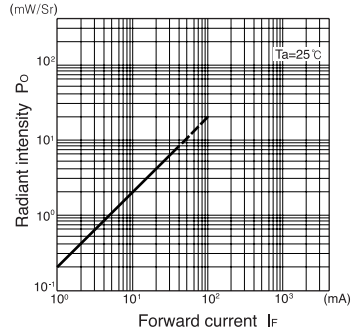
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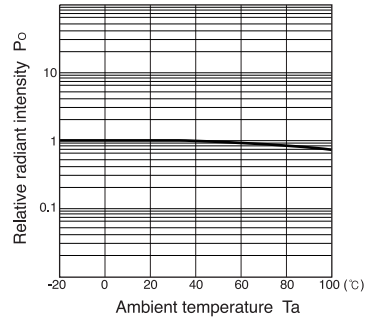
Power dissipation Vs. Ambient temperature



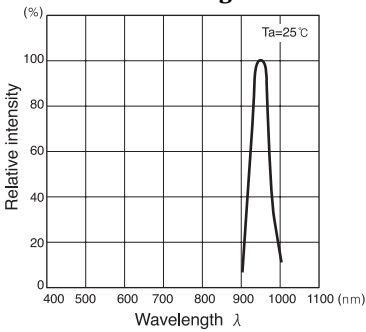
Radiant intensity Vs. Forward current



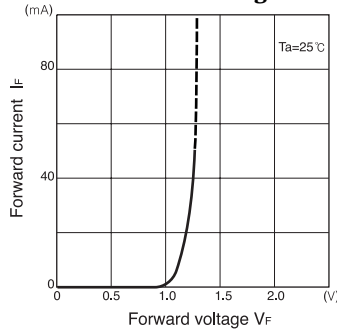
Relative radiant intensity Vs. Ambient temperature



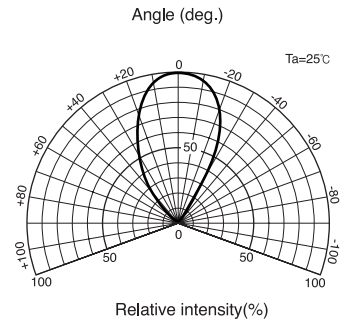
Relative intensity Vs. Wavelength



Forward current vs. Forward voltage



Radiant Pattern



Relative radiant intensity Vs. Distance

